

the data or gate drive IC 17 is installed on a polymer film 19, and the polymer
Q1 film 19 is connected with the lower substrate 20 and the gate or source PCB 31
Cont or 33 via an anisotropic conductive films 18.

Please **rewrite the paragraph beginning on page 12, line 8**, as follows:

As shown, adjacent to each gate pad 128 and each source pad 130, a
gate dummy pad 157b and a source dummy pad 157a are formed respectively.
Q2 Across the source pads 130 and the source dummy pads 157a, a first repair
wire 150a is formed with an insulating layer (not shown) interposed between
the pads and the repair wire. Similarly, a second repair wire 150b is formed
across the gate pads 128 and the gate dummy pads 157b with the insulating
layer interposed between the pads and the repair wire. The source and gate
dummy pads 157a and 157b are electrically connected via a dummy wire 137b
that has the same material as the gate transmitting wires 137.

Please **rewrite the paragraph beginning on page 12, line 16**, as
follows:

Since a mechanical impact or vibration acts on the upper substrate in
Q3 the above-mentioned scribing and breaking process, open defects occur in the
gate transmitting wire 137 along first and second edges 161a and 161b of the
upper substrate 110. For example, first and second open defects F₁ and F₂ of

*Q3
cont*
the last gate transmitting wire 137a occur, respectively, near the first and second edges 161a and 161b of the upper substrate 110.

Please rewrite the paragraph beginning on page 18, line 7, as follows:

Q4
Next, a gate insulating layer 190 are formed to cover the gate lines and the gate transmitting wires 137. Thereafter, not shown in Figure 16A, source and drain electrodes, and a plurality of data lines 125 (see Figure 14) will be formed on the gate insulating layer 190. The gate, source and drain electrodes are included in a switching device such as a thin film transistor (TFT).

Please rewrite the paragraph beginning on page 18, line 18, and ending on page 19, line 1, as follows:

Q5
In Figure 16B, between the dummy patterns 180b and the passivation layer 192, auxiliary dummy patterns 185 are interposed in shape of islands such that a first height "a" measured from the upper substrate 110 to the auxiliary dummy pattern 185 is smaller than a second height "b" measured from the upper substrate 110 to the gate transmitting wire 137. In this case, since the auxiliary dummy patterns 185 and the dummy patterns 180b absorb most of the scribing and breaking force in the scribing and breaking process, the gate transmitting wires 137 are protected from the mechanical impact or vibration of a cutting device used for the scribing and breaking process.
